

# Nandakishor Yadav

## List of Publications by Citations

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31  
papers

198  
citations

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h-index

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g-index

38  
ext. papers

264  
ext. citations

1.9  
avg, IF

3.54  
L-index

#	Paper	IF	Citations
31	On-Chip Adaptive Body Bias for Reducing the Impact of NBTI on 6T SRAM Cells. <i>IEEE Transactions on Semiconductor Manufacturing</i> , <b>2018</b> , 31, 242-249	2.6	27
30	Stable, Reliable, and Bit-Interleaving 12T SRAM for Space Applications: A Device Circuit Co-Design. <i>IEEE Transactions on Semiconductor Manufacturing</i> , <b>2017</b> , 30, 276-284	2.6	26
29	Systematically optimized coenzyme q10-loaded novel proniosomal formulation for treatment of photo-induced aging in mice: characterization, biocompatibility studies, biochemical estimations and anti-aging evaluation. <i>Journal of Drug Targeting</i> , <b>2016</b> , 24, 257-71	5.4	23
28	Systematically Optimized Ketoprofen-Loaded Novel Proniosomal Formulation for Periodontitis: In Vitro Characterization and In Vivo Pharmacodynamic Evaluation. <i>AAPS PharmSciTech</i> , <b>2017</b> , 18, 1863-1880 <sup>3,9</sup>	3.9	13
27	Analog/RF characteristics of a 3D-Cyl underlap GAA-TFET based on a Ge source using fringing-field engineering for low-power applications. <i>Journal of Computational Electronics</i> , <b>2018</b> , 17, 1650-1657	1.8	12
26	Process Variation and NBTI Resilient Schmitt Trigger for Stable and Reliable Circuits. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2018</b> , 18, 546-554	1.6	12
25	A Novel FPGA Accelerator Design for Real-Time and Ultra-Low Power Deep Convolutional Neural Networks Compared With Titan X GPU. <i>IEEE Access</i> , <b>2020</b> , 8, 105455-105471	3.5	11
24	An efficient NBTI sensor and compensation circuit for stable and reliable SRAM cells. <i>Microelectronics Reliability</i> , <b>2018</b> , 87, 15-23	1.2	11
23	Analysis of trap-assisted tunnelling in asymmetrical underlap 3D-cylindrical GAA-TFET based on hetero-spacer engineering for improved device reliability. <i>Micro and Nano Letters</i> , <b>2017</b> , 12, 982-986	0.9	10
22	Novel CNN-Based AP2D-Net Accelerator: An Area and Power Efficient Solution for Real-Time Applications on Mobile FPGA. <i>Electronics (Switzerland)</i> , <b>2020</b> , 9, 832	2.6	7
21	NMOS only Schmitt trigger circuit for NBTI resilient CMOS circuits. <i>Electronics Letters</i> , <b>2018</b> , 54, 868-870 <sup>1,1</sup>	1.1	6
20	NBTI aware IG-FinFET based SRAM design using adaptable trip-point sensing technique <b>2014</b> ,		5
19	SUBHDIP: process variations tolerant subthreshold Darlington pair-based NBTI sensor circuit. <i>IET Computers and Digital Techniques</i> , <b>2019</b> , 13, 243-249	0.9	5
18	Low-Power RTL Code Generation for Advanced CNN Algorithms toward Object Detection in Autonomous Vehicles. <i>Electronics (Switzerland)</i> , <b>2020</b> , 9, 478	2.6	5
17	Double-gate FinFET process variation aware 10T SRAM cell topology design and analysis <b>2013</b> ,		3
16	A novel stability and process sensitivity driven model for optimal sized FinFET based SRAM. <i>Microelectronics Reliability</i> , <b>2015</b> , 55, 1131-1143	1.2	2
15	Design of a Voltage to Time Converter with High Conversion Gain for Reliable and Secure Autonomous Vehicles. <i>Electronics (Switzerland)</i> , <b>2020</b> , 9, 384	2.6	2

14	A New Sensitivity-Driven Process Variation Aware Self-Repairing Low-Power SRAM Design <b>2014</b> ,		2
13	Subthreshold darlington pair based NBTI sensor for reliable CMOS circuits <b>2017</b> ,		2
12	LISOCHIN: An NBTI Degradation Monitoring Sensor for Reliable CMOS Circuits. <i>Communications in Computer and Information Science</i> , <b>2017</b> , 441-451	0.3	2
11	Impact of varying carbon concentration in SiC S/D asymmetric dual-k spacer for high performance and reliable FinFET. <i>Journal of Semiconductors</i> , <b>2018</b> , 39, 104001	2.3	2
10	Ultra-Low Power and High-Throughput SRAM Design to Enhance AI Computing Ability in Autonomous Vehicles. <i>Electronics (Switzerland)</i> , <b>2021</b> , 10, 256	2.6	2
9	Symmetric dual gate insulator-based FinFET module and design window for reliable circuits. <i>Micro and Nano Letters</i> , <b>2019</b> , 14, 317-322	0.9	1
8	Sensitive, Linear, Robust Current-To-Time Converter Circuit for Vehicle Automation Application. <i>Electronics (Switzerland)</i> , <b>2020</b> , 9, 490	2.6	1
7	A sensitivity driven 10T SRAM cell to mitigate process variation via selective back-gate biasing <b>2014</b> ,		1
6	Self-restoring PVT aware independently-controlled Gate FinFET based 10T SRAM cell <b>2013</b> ,		1
5	Stable, Low Power and Bit-Interleaving Aware SRAM Memory for Multi-Core Processing Elements. <i>Electronics (Switzerland)</i> , <b>2021</b> , 10, 2724	2.6	1
4	A Reactive and On-Chip Sensor Circuit for NBTI and PBTI Resilient SRAM Design. <i>Electronics (Switzerland)</i> , <b>2020</b> , 9, 326	2.6	0
3	Design and Development of BTI Model and 3D InGaAs HEMT-Based SRAM for Reliable and Secure Internet of Things Application. <i>Electronics (Switzerland)</i> , <b>2020</b> , 9, 469	2.6	0
2	A Novel Ultra-Low Power 8T SRAM-Based Compute-in-Memory Design for Binary Neural Networks. <i>Electronics (Switzerland)</i> , <b>2021</b> , 10, 2181	2.6	0
1	Design and Analysis of Cyl GAA-TFET-Based Cross-Coupled Voltage Doubler Circuit. <i>Lecture Notes in Electrical Engineering</i> , <b>2021</b> , 69-79	0.2	